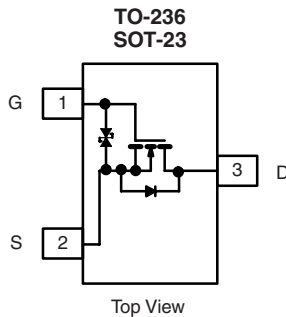


N-Channel 60-V (D-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (mA)
60	2 at $V_{GS} = 10$ V	300



2N7002K (7K)*
* Marking Code

Ordering Information: 2N7002K-T1
2N7002K-T1-E3 (Lead (Pb)-free)
2N7002K-T1-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- Low On-Resistance: 2 Ω
- Low Threshold: 2 V (typ.)
- Low Input Capacitance: 25 pF
- Fast Switching Speed: 25 ns
- Low Input and Output Leakage
- TrenchFET[®] Power MOSFET
- 2000 V ESD Protection



RoHS*
COMPLIANT
HALOGEN
FREE
Available

BENEFITS

- Low Offset Voltage
- Low-Voltage Operation
- Easily Driven Without Buffer
- High-Speed Circuits
- Low Error Voltage

APPLICATIONS

- Direct Logic-Level Interface: TTL/CMOS
- Drivers: Relays, Solenoids, Lamps, Hammers, Display, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	± 20	
Continuous Drain Current ($T_J = 150$ °C) ^b	I_D	$T_A = 25$ °C	300
		$T_A = 100$ °C	190
Pulsed Drain Current ^a	I_{DM}	800	mA
Power Dissipation ^b	P_D	$T_A = 25$ °C	0.35
		$T_A = 100$ °C	0.14
Maximum Junction-to-Ambient ^b	R_{thJA}	350	°C/W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

Notes:

- a. Pulse width limited by maximum junction temperature.
b. Surface Mounted on FR4 board.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

SPECIFICATIONS $T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Limits			Unit
			Min.	Typ. ^a	Max.	
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 10\text{ }\mu\text{A}$	60			V
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1		2.5	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			± 10	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 15\text{ V}$			1	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}$			± 150	nA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 10\text{ V}, T_J = 85\text{ }^\circ\text{C}$			± 1000	
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 5\text{ V}$			± 100	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}$			10	μA
		$V_{DS} = 50\text{ V}, V_{GS} = 0\text{ V}, T_J = 85\text{ }^\circ\text{C}$			100	
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$			500	
On-State Drain Current ^a	$I_{D(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 7.5\text{ V}$	800			mA
		$V_{GS} = 4.5\text{ V}, V_{DS} = 10\text{ V}$	500			
Drain-Source On-Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 500\text{ mA}$			2	Ω
		$V_{GS} = 4.5\text{ V}, I_D = 200\text{ mA}$			4	
Forward Transconductance ^a	g_{fs}	$V_{DS} = 10\text{ V}, I_D = 200\text{ mA}$	100			mS
Diode Forward Voltage	V_{SD}	$I_S = 200\text{ mA}, V_{GS} = 0\text{ V}$			1.3	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}$ $I_D \cong 250\text{ mA}$		0.4	0.6	nC
Input Capacitance	C_{iss}	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}$ $f = 1\text{ MHz}$		30		pF
Output Capacitance	C_{oss}			6		
Reverse Transfer Capacitance	C_{rss}			2.5		
Switching^{a, b, c}						
Turn-On Time	$t_{d(on)}$	$V_{DD} = 30\text{ V}, R_L = 150\text{ }\Omega$ $I_D \cong 200\text{ mA}, V_{GEN} = 10\text{ V}, R_G = 10\text{ }\Omega$			25	ns
Turn-Off Time	$t_{d(off)}$				35	

Notes:

- a. For DESIGN AID ONLY, not subject to production testing.
 b. Pulse test: $PW \leq 300\text{ }\mu\text{s}$ duty cycle $\leq 2\%$.
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.